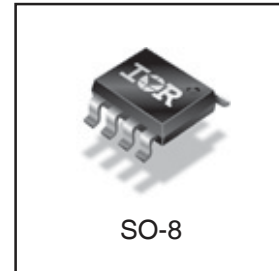
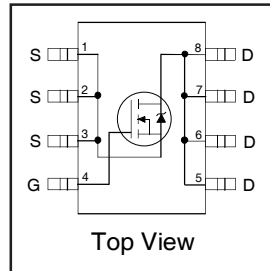


HEXFET® Power MOSFET

V_{DS}	25	V
$R_{DS(on) max}$ (@ $V_{GS} = 10V$)	2.7	mΩ
Q_g (typical)	35	nC
I_D (@ $T_A = 25^\circ C$)	25	A



Applications

- Synchronous MOSFET for Notebook Processor Power
- Synchronous Rectifier MOSFET for Isolated DC-DC Converters

Features

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification

⇒

Benefits

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF8252PbF-1	SO-8	Tape and Reel	4000	IRF8252TRPbF-1

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	25	V
V_{GS}	Gate-to-Source Voltage	±20	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	25	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	20	
I_{DM}	Pulsed Drain Current ①	200	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.6	
	Linear Derating Factor	0.02	W/°C
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ②	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④ ⑤	—	50	

Notes ① through ⑤ are on page 10

Static @ T_J = 25°C (unless otherwise specified)

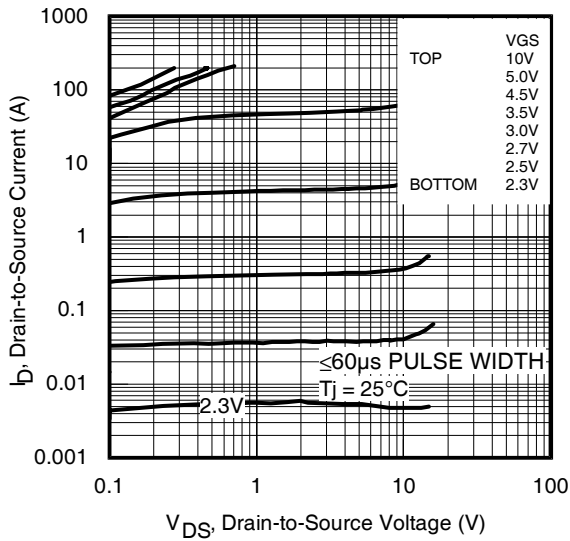
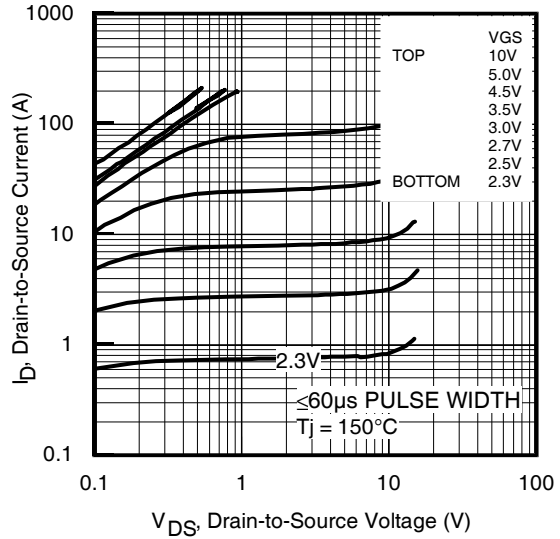
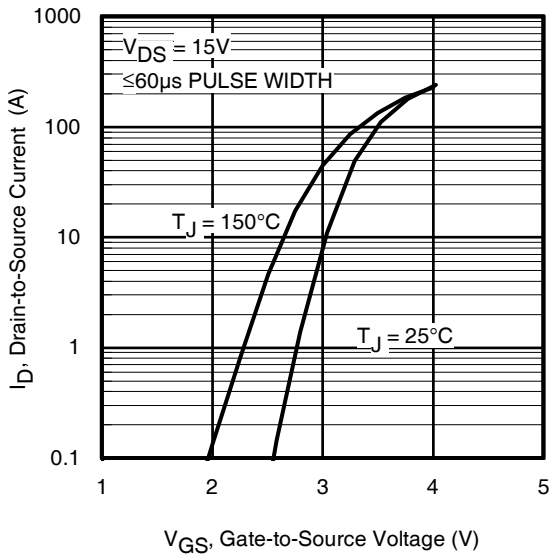
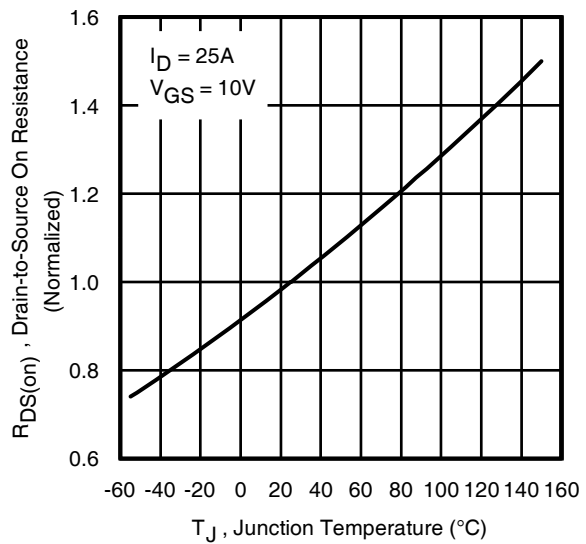
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	25	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.018	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	2.0	2.7	mΩ	V _{GS} = 10V, I _D = 25A ③
		—	2.9	3.7		V _{GS} = 4.5V, I _D = 20A ③
V _{GS(th)}	Gate Threshold Voltage	1.35	1.80	2.35	V	V _{DS} = V _{GS} , I _D = 100μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	-6.67	—	mV/°C	V _{DS} = V _{GS} , I _D = 100μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
		—	—	150		V _{DS} = 20V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	89	—	—	S	V _{DS} = 13V, I _D = 20A
Q _g	Total Gate Charge	—	35	53	nC	V _{DS} = 13V V _{GS} = 4.5V I _D = 20A See Figs. 15 & 16
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	10	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	4.6	—		
Q _{gd}	Gate-to-Drain Charge	—	12	—		
Q _{godr}	Gate Charge Overdrive	—	8.9	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	16	—	nC	V _{DS} = 16V, V _{GS} = 0V
Q _{oss}	Output Charge	—	26	—	nC	V _{DS} = 16V, V _{GS} = 0V
R _g	Gate Resistance	—	0.61	1.22	Ω	
t _{d(on)}	Turn-On Delay Time	—	23	—	ns	V _{DD} = 13V, V _{GS} = 4.5V I _D = 20A R _G = 1.8Ω See Fig. 18
t _r	Rise Time	—	32	—		
t _{d(off)}	Turn-Off Delay Time	—	19	—		
t _f	Fall Time	—	12	—		
C _{iss}	Input Capacitance	—	5305	—	pF	V _{GS} = 0V V _{DS} = 13V f = 1.0MHz
C _{oss}	Output Capacitance	—	1340	—		
C _{rss}	Reverse Transfer Capacitance	—	725	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	231	mJ
I _{AR}	Avalanche Current ①	—	20	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	200	A	
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 20A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	19	29	ns	T _J = 25°C, I _F = 20A, V _{DD} = 13V
Q _{rr}	Reverse Recovery Charge	—	12	18	nC	di/dt = 230A/μs ③
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

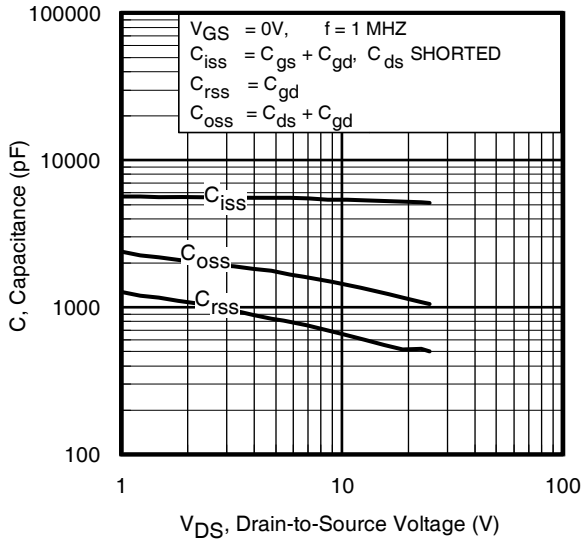


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

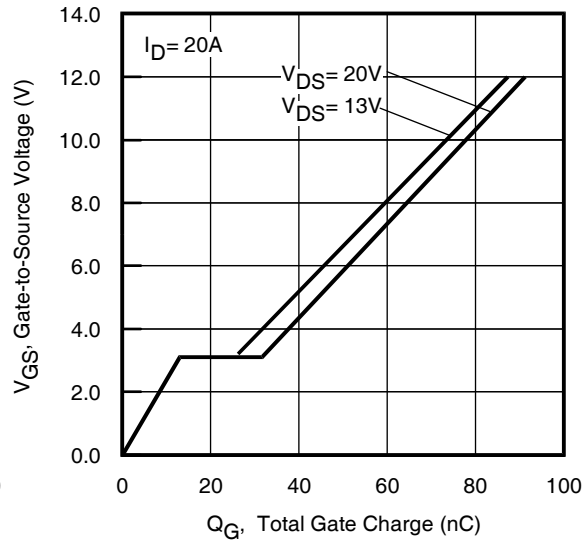


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

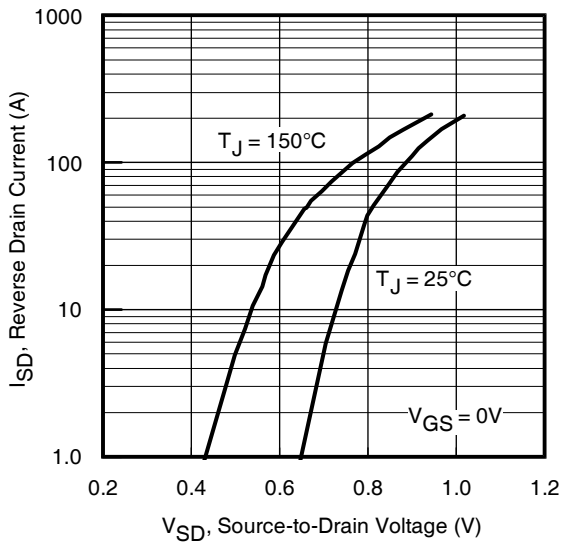


Fig 7. Typical Source-Drain Diode Forward Voltage

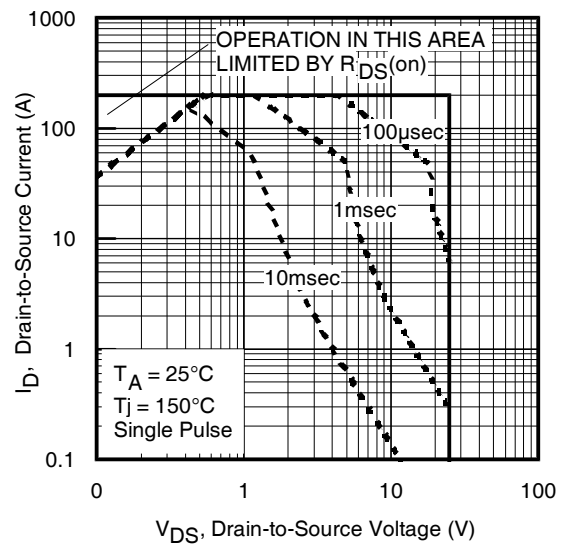


Fig 8. Maximum Safe Operating Area

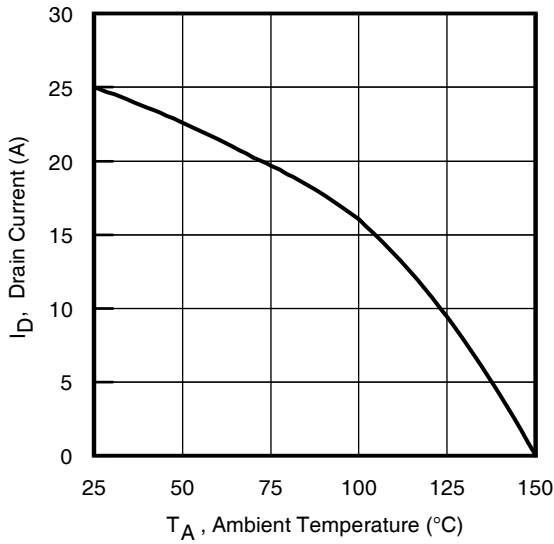


Fig 9. Maximum Drain Current vs. Ambient Temperature

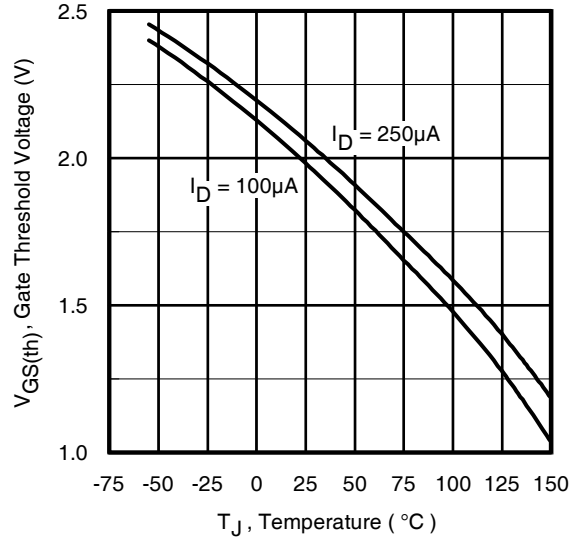


Fig 10. Threshold Voltage vs. Temperature

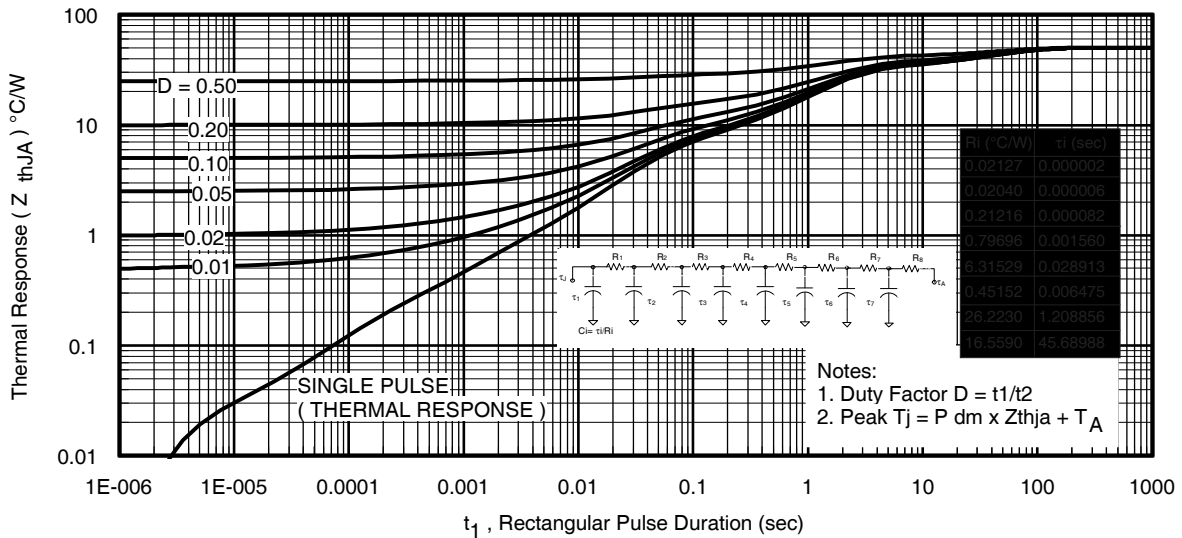
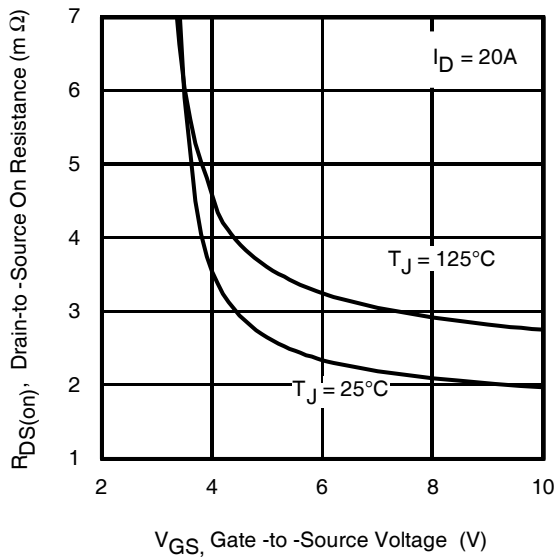
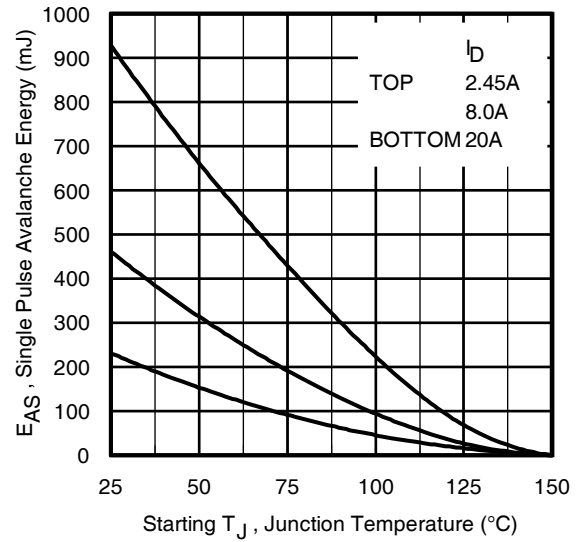
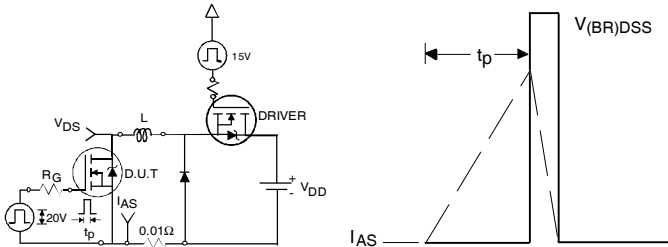
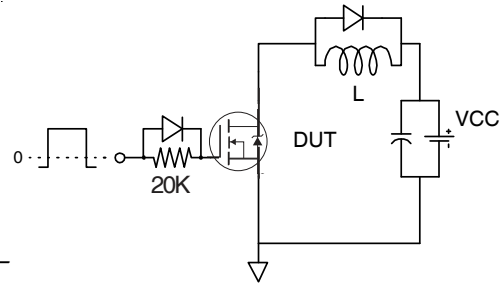
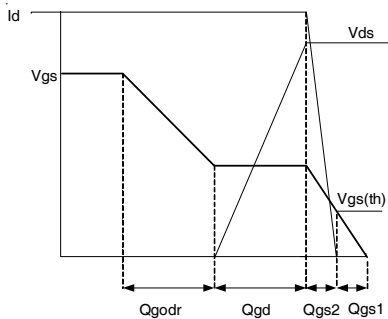
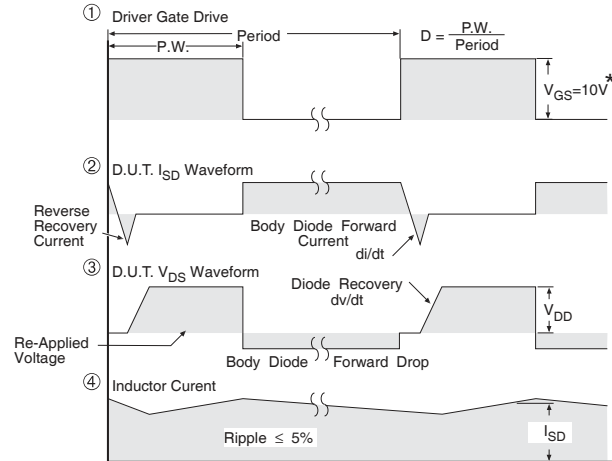
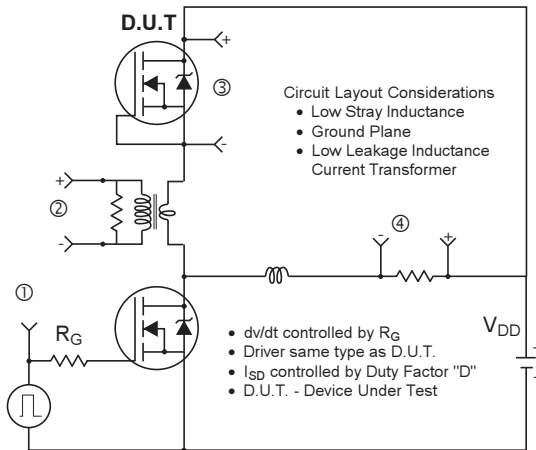


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14. Unclamped Inductive Test Circuit and Waveform

Fig 15. Gate Charge Test Circuit

Fig 16. Gate Charge Waveform



* $V_{GS} = 5V$ for Logic Level Devices

Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

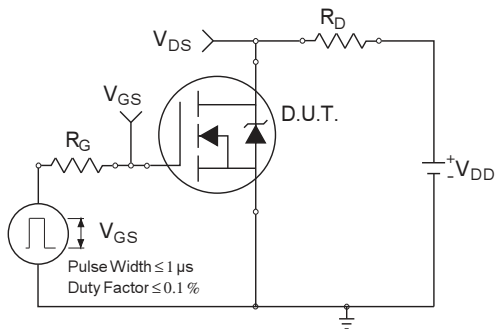


Fig 18a. Switching Time Test Circuit

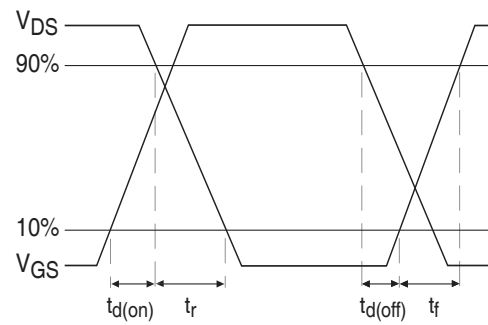
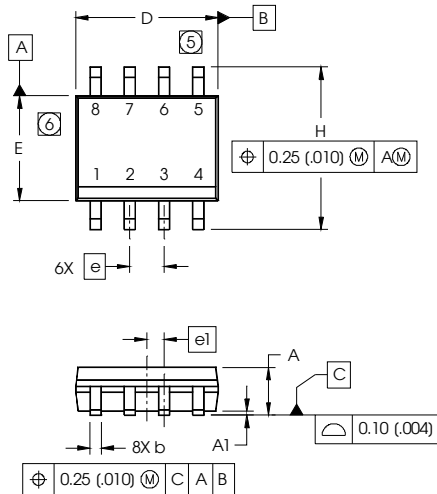


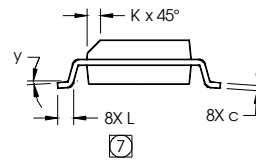
Fig 18b. Switching Time Waveforms

SO-8 Package Outline (MOSFET & Fetky)

Dimensions are shown in millimeters (inches)



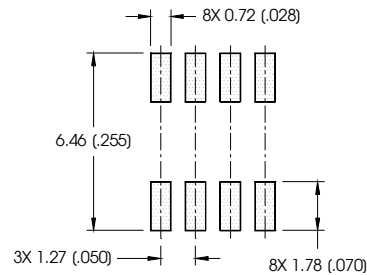
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

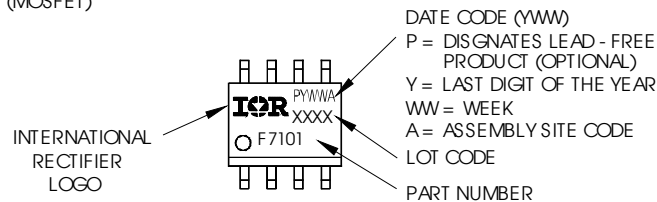
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT

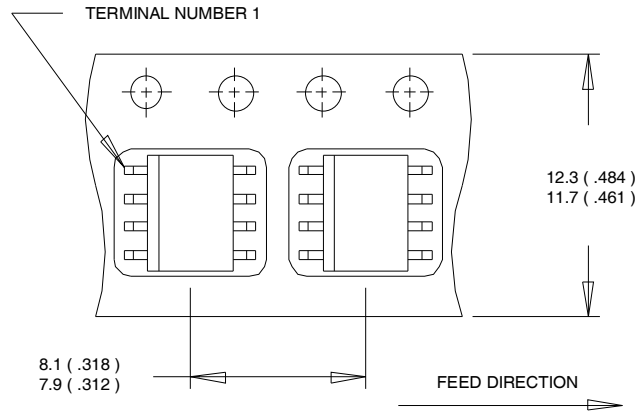


SO-8 Part Marking Information

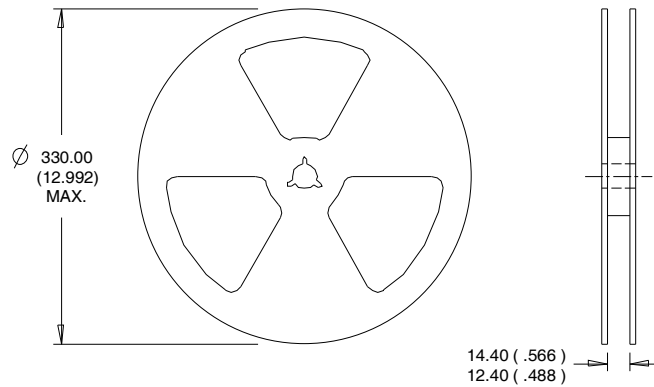
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))


- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification information[†]

Qualification level	Industriid (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	SO-8	M5L1 (per JEDEC J-STD-020D ^{††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.12\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 20\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.
- ⑤ R_θ is measured at T_J of approximately 90°C .

Revision History

Date	Comments
10/16/2014	<ul style="list-style-type: none"> • Corrected part number from "IRF8252PbF-1" to "IRF8252TRPbF-1" -all pages • Removed the "IRF8252PbF-1" bulk part number from ordering information on page1